

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L83	51	((strain or strained) adj substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:43
L84	0	((((strain or strained) adj substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:43
L85	3	((((strain or strained) adj substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:44
L86	22	((((strain or strained) near substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:44
L87	0	((((strain or strained) near substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)) and (high-k))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:44
L88	0	((((strain or strained) near substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)) and ((high near k) or (high-k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:44
L89	3	((((strain or strained) near2 substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)) and ((high near k) or (high-k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:45
L90	11	((((strain or strained) near3 substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)) and ((high near k) or (high-k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:46
L91	0	((((strain or strained) near3 substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)).clm. and ((high near k) or (high-k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 18:46

L92	0	((((strain or strained) near5 substrate) with (si or silicon) with (epi or epitaxy or epitaxial or epitaxially)).clm. and ((high near k) or (high-k))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:24
L93	645	substrate with (strain or strained) near (si or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:25
L94	48	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:25
L95	10	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)) and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:27
L96	6	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)) and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant)) and (epi or epitaxy or epitaxial)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:28
L97	6	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)) and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant)) and (epi or epitaxy or epitaxial or epitaxially)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:28
L98	1	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)) and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant)) and (epi or epitaxy or epitaxial or epitaxially).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:29
L99	0	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)). clm. and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant)) and (epi or epitaxy or epitaxial or epitaxially)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:29

L100	6	(substrate with (strain or strained) near (si or silicon)) with (gate near (oxide or dielectric or insulating)) and ((gate near (oxide or dielectric or insulating)) with (dielectric adj constant)) and (epi or epitaxy or epitaxial or epitaxially)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:30
L101	27368	(strain or strained).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:30
L102	20	(strain or strained).clm. and ((high near k) or high-k).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:30
L103	6	(strain or strained).clm. and ((high near k) or high-k).clm. and (epi or epitaxy or epitaxial or epitaxially).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:31
L104	0	(strain or strained).clm. and ((high near k) or high-k).clm. and (epi or epitaxy or epitaxial or epitaxially).clm. and (gate adj (oxide or dielectric or insulating)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:31
L105	4	(strain or strained).clm. and ((high near k) or high-k).clm. and (epi or epitaxy or epitaxial or epitaxially) and (gate adj (oxide or dielectric or insulating)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:36
L106	1	(strain or strained).clm. and ((high near k) or high-k).clm. and (epi or epitaxy or epitaxial or epitaxially) and (gate adj (oxide or dielectric or insulating)).clm. and (dielectric adj constant).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:33
L107	1	(strain or strained).clm. and ((high near k) or high-k).clm. and (epi or epitaxy or epitaxial or epitaxially) and (gate adj (oxide or dielectric or insulating)).clm. and (dielectric adj constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:33
L108	1314	(substrate near10 (strain or strained)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:37

L109	875	(substrate near5 (strain or strained)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:37
L110	13	(substrate near5 (strain or strained)).clm. and ((gate adj (oxide or dielectric)) near10 ((high-k) or (high near k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:38
L111	0	(substrate near5 (strain or strained)).clm. and ((gate adj (oxide or dielectric)) near10 ((high-k) or (high near k))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:38
L112	0	(substrate near5 (strain or strained)).clm. and ((gate adj (oxide or dielectric or insulating)) near10 ((high-k) or (high near k))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:38
L113	0	(substrate near5 (strain or strained)).clm. and ((gate adj (oxide or dielectric or insulating)) with ((high-k) or (high near k))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:38
L114	20	(substrate near5 (strain or strained)).clm. and ((gate adj (oxide or dielectric or insulating)) with ((high-k) or (high near k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:38
L115	42	(substrate near5 (strain or strained)) and ((gate adj (oxide or dielectric or insulating)) with ((high-k) or (high near k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:39
L116	30	(substrate near5 (strain or strained)) and ((gate adj (oxide or dielectric or insulating)) near5 ((high-k) or (high near k)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/18 21:39